

Shoji Ishibashi

List of Publications by Year in descending order

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220
papers

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citations

101384

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225
docs citations

225
times ranked

4543
citing authors

#	ARTICLE	IF	CITATIONS
1	Charge-transport in tin-iodide perovskite CH ₃ NH ₃ SnI ₃ : origin of high conductivity. Dalton Transactions, 2011, 40, 5563.	1.6	342
2	Weyl Node and Spin Texture in Trigonal Tellurium and Selenium. Physical Review Letters, 2015, 114, 206401.	2.9	195
3	A Possible Ground State and Its Electronic Structure of a Mother Material (LaOFeAs) of New Superconductors. Journal of the Physical Society of Japan, 2008, 77, 053709.	0.7	152
4	The origins and properties of intrinsic nonradiative recombination centers in wide bandgap GaN and AlGaN. Journal of Applied Physics, 2018, 123, .	1.1	112
5	<i>Ab initio</i> calculations of electric-field-induced stress profiles for diamond. $\langle B \rangle$ $\langle N \rangle$ superlattices. Physical Review B, 2007, 76, .	1.1	84
6	Proton tautomerism for strong polarization switching. Nature Communications, 2017, 8, 14426.	5.8	83
7	Observation of Three-Dimensional Fermi Surfaces in a Single-Component Molecular Metal, [Ni(tmtdt) ₂]. Journal of the American Chemical Society, 2004, 126, 10518-10519.	6.6	76
8	A Single-Component Molecular Superconductor. Journal of the American Chemical Society, 2014, 136, 7619-7622.	6.6	75
9	First-Principles Study of Magnetocrystalline Anisotropy and Magnetization in NdFe ₁₂ , NdFe ₁₁ Ti, and NdFe ₁₁ TiN. Journal of the Physical Society of Japan, 2014, 83, 043702.	0.7	74
10	First-Principles Electronic Structure of Solid Picene. Journal of the Physical Society of Japan, 2009, 78, 113704.	0.7	73
11	Nitrogen vacancies as a common element of the green luminescence and nonradiative recombination centers in Mg-implanted GaN layers formed on a GaN substrate. Applied Physics Express, 2017, 10, 061002.	1.1	70
12	Vacancy-type defects and their annealing behaviors in Mg-implanted GaN studied by a monoenergetic positron beam. Physica Status Solidi (B): Basic Research, 2015, 252, 2794-2801.	0.7	65
13	<i>Ab Initio</i> Electronic-Structure Calculations for \pm -(BEDT-TTF) ₂ I ₃ . Journal of the Physical Society of Japan, 2006, 75, 015005.	0.7	64
14	Vacancy-oxygen complexes and their optical properties in AlN epitaxial films studied by positron annihilation. Journal of Applied Physics, 2009, 105, .	1.1	63
15	<i>Ab initio</i> local stress and its application to Al (111) surfaces. Physical Review B, 2010, 81, .	1.1	62
16	First-principles study on stability and magnetism of NdFe ₁₁ M and NdFe ₁₁ MN for $M = \text{Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn}$. Journal of Applied Physics, 2016, 120, .	1.1	62
17	Carrier Trapping by Vacancy-type Defects in Mg-implanted GaN Studied Using Monoenergetic Positron Beams. Physica Status Solidi (B): Basic Research, 2018, 255, 1700521.	0.7	60
18	Noncollinear Magnetism and Spin-Orbit Coupling in $\text{Pyrochlore Oxide } \langle \text{Os} \rangle \langle \text{O} \rangle$. Physical Review Letters, 2018, 121, 087201.	2.9	59

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19	Large electron capture-cross-section of the major nonradiative recombination centers in Mg-doped GaN epilayers grown on a GaN substrate. Applied Physics Letters, 2018, 112, .	1.5	55
20	First-principles study of the rectifying properties of PtTiO_3 . Physical Review B, 2009, 80, .	1.1	54
21	First-principles structural optimization and electronic structure of the superconductor picene for various potassium doping levels. Physical Review B, 2011, 84, .	1.1	54
22	Jahn-Teller distortion and magnetic structure in LaMnO_3 . A first-principles theoretical study with full structure optimizations. Physical Review B, 2010, 82, .	1.1	53
23	Native cation vacancies in Si-doped AlGaIn studied by monoenergetic positron beams. Journal of Applied Physics, 2012, 111, .	1.1	53
24	Polarization Switching Ability Dependent on Multidomain Topology in a Uniaxial Organic Ferroelectric. Nano Letters, 2014, 14, 239-243.	4.5	53
25	Point defects in group-III nitride semiconductors studied by positron annihilation. Journal of Crystal Growth, 2009, 311, 3075-3079.	0.7	51
26	Hydrogen-Bonded Small-Molecular Crystals Yielding Strong Ferroelectric and Antiferroelectric Polarizations. Journal of the Physical Society of Japan, 2020, 89, 051009.	0.7	51
27	XBN as the best intercalation compound among XBN magnet C , N , O , and F for strong permanent. First-principles study. Physical Review B, 2015, 92, .	1.1	50
28	Static dielectric response and Born effective charge of BN nanotubes from ab initio finite electric field calculations. Physical Review B, 2007, 75, .	1.1	45
29	Vacancy Clusters on Surfaces of Au Nanoparticles Embedded in MgO. Physical Review Letters, 1999, 83, 4586-4589.	2.9	44
30	Ionic versus Electronic Ferroelectricity in Donor-Acceptor Molecular Sequences. Chemistry Letters, 2014, 43, 26-35.	0.7	43
31	Electronic Structures of Single Component Molecular Metals Based on <i>Ab initio</i> Calculation. Journal of the Physical Society of Japan, 2008, 77, 024702.	0.7	41
32	Strong polarization switching with low-energy loss in hydrogen-bonded organic antiferroelectrics. Chemical Science, 2018, 9, 425-432.	3.7	41
33	Construction of Electron-Positron Momentum Density from Pseudo-Wavefunctions with Better Accuracy. Materials Science Forum, 2004, 445-446, 401-403.	0.3	38
34	Annealing properties of vacancy-type defects in ion-implanted GaN studied by monoenergetic positron beams. Journal of Applied Physics, 2007, 102, 084505.	1.1	38
35	Ab Initio Electronic Structure Calculation for Single-Component Molecular Conductor $\text{Au}(\text{tmdt})_2$ (tmdt = Trimethylenetetrafulvalenedithiolate). Journal of the Physical Society of Japan, 2005, 74, 843-846.	0.7	37
36	Analysis of Screening Mechanisms for Polar Discontinuity for $\text{LaAlO}_3/\text{SrTiO}_3$ Thin Films Based on Ab initio Calculations. Journal of the Physical Society of Japan, 2008, 77, 104706.	0.7	37

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37	First-principles study of spontaneous polarization in tetrathiafulvalene-p-chloranil (TTF-CA). <i>Physica B: Condensed Matter</i> , 2010, 405, S338-S340.	1.3	37
38	Ab initio electronic structure of solid coronene: Differences from and commonalities to picene. <i>Physical Review B</i> , 2011, 84, .	1.1	37
39	Single-Component Molecular Metals as Multiband Systems. <i>Journal of the Physical Society of Japan</i> , 2008, 77, 023714.	0.7	36
40	Tuning the Magnetic Dimensionality by Charge Ordering in the Molecular TMTTF Salts. <i>Physical Review Letters</i> , 2012, 108, 096402.	2.9	36
41	Study of Superconductors with High Transition Temperature by Positron Annihilation. <i>Japanese Journal of Applied Physics</i> , 1987, 26, L688-L689.	0.8	35
42	First-principles analysis of the optical properties of structural disorder in SiO_2 . <i>Physical Review B</i> , 2008, 77, .	1.1	35
43	Crystal structures and physical properties of single-component molecular conductors consisting of nickel and gold complexes with bis(trifluoromethyl)tetrathiafulvalenedithiolate ligands. <i>Journal of Materials Chemistry</i> , 2005, 15, 155.	6.7	34
44	Experimental evidence for fast cluster formation of chain oxygen vacancies in $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ as the origin of the fishtail anomaly. <i>Solid State Communications</i> , 1999, 112, 245-249.	0.9	33
45	Ab initio pseudopotential calculation for TTF-TCNQ and TSeF-TCNQ. <i>Physical Review B</i> , 2000, 62, 7839-7844.	1.1	33
46	Electronic Structure of Novel Superconductor $\text{Ca}_4\text{Al}_2\text{O}_6\text{Fe}_2\text{As}_2$. <i>Journal of the Physical Society of Japan</i> , 2010, 79, 123713.	0.7	33
47	Defect characterization in Mg-doped GaN studied using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	33
48	First-principles calculation of positron states and annihilation parameters for group-III nitrides. <i>Journal of Physics: Conference Series</i> , 2014, 505, 012010.	0.3	33
49	Single-component molecular conductor $[\text{Pt}(\text{dmdt})_2]$ a three-dimensional ambient-pressure molecular Dirac electron system. <i>Chemical Communications</i> , 2019, 55, 3327-3330.	2.2	31
50	Anion vacancies in CuInSe_2 . <i>Thin Solid Films</i> , 2001, 387, 129-134.	0.8	30
51	Effect of solid-solution strengthening on deformation mechanisms and strain hardening in medium-entropy V1-Cr CoNi alloys. <i>Journal of Materials Science and Technology</i> , 2022, 108, 270-280.	5.6	30
52	Characterization of superconducting alkali and alkaline-earth fullerenes prepared by thermal decomposition of azides. <i>Journal of Physics and Chemistry of Solids</i> , 1993, 54, 1667-1673.	1.9	28
53	Annealing Behavior of Vacancy-Type Defects in Mg- and H-implanted GaN Studied Using Monoenergetic Positron Beams. <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1900104.	0.7	27
54	Positron Annihilation Spectroscopy on Nitride-Based Semiconductors. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JJ02.	0.8	26

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55	Piezoelectricity of strongly polarized ferroelectrics in prototropic organic crystals. <i>Journal of Materials Chemistry C</i> , 2018, 6, 4714-4719.	2.7	26
56	Room temperature photoluminescence lifetime for the near-band-edge emission of epitaxial and ion-implanted GaN on GaN structures. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC0802.	0.8	25
57	Vacancy-type defects in Er-doped GaN studied by a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2008, 103, 104505.	1.1	24
58	Vacancy-type defects in Mg-doped InN probed by means of positron annihilation. <i>Journal of Applied Physics</i> , 2009, 105, .	1.1	24
59	Structure-Property Relationship of Supramolecular Ferroelectric [H ₆₆ mbp][Hca] Accompanied by High Polarization, Competing Structural Phases, and Polymorphs. <i>Chemistry - A European Journal</i> , 2014, 20, 17515-17522.	1.7	24
60	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	24
61	Optically active vacancies in GaN grown on Si substrates probed using a monoenergetic positron beam. <i>Applied Physics Letters</i> , 2014, 104, 082110.	1.5	22
62	Vacancies and electron trapping centers in acidic ammonothermal GaN probed by a monoenergetic positron beam. <i>Journal of Crystal Growth</i> , 2016, 448, 117-121.	0.7	22
63	Field-Induced Antipolar-Polar Structural Transformation and Giant Electrostriction in Organic Crystal. <i>Journal of the American Chemical Society</i> , 2018, 140, 3842-3845.	6.6	22
64	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. <i>Scientific Reports</i> , 2020, 10, 17349.	1.6	22
65	Vacancy-Boron Complexes in Plasma Immersion Ion-Implanted Si Probed by a Monoenergetic Positron Beam. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 051301.	0.8	21
66	Spin-orbital frustration in molybdenum pyrochlores A ₂ Mo ₂ O ₇ (A=rare earth). <i>Physical Review B</i> , 2013, 88, .	1.1	21
67	Vacancy-type defects in Al ₂ O ₃ /GaN structure probed by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	21
68	Positron lifetime spectroscopy on the high T _c superconductor Ba ₂ YCu ₃ O _{7-δ} . <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1988, 128, 387-390.	0.9	20
69	Positron states in C ₆₀ and potassium-doped C ₆₀ crystals. <i>Journal of Physics Condensed Matter</i> , 1992, 4, L169-L177.	0.7	20
70	Vacancy-type defects in In _x Ga _{1-x} N alloys probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	20
71	First-principles calculations for the magnetic phase diagram in electron-doped CaMnO ₃ under compressive and tensile strains. <i>Physical Review B</i> , 2010, 81, .	1.1	19
72	Slab Thickness Dependence of Rashba Splitting on Au(111) Surface: First-Principles and Model Analyses. <i>Journal of the Physical Society of Japan</i> , 2011, 80, 074713.	0.7	19

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73	Origin of surface stress on late transition metal surfaces: <i>Ab initio</i> local stress and tight-binding model. <i>Physical Review B</i> , 2013, 87, .	1.1	19
74	Positron lifetime in oxide superconductors $\text{YBa}_2(\text{Cu}_{1-x}\text{M}_x)\text{O}_{7-y}$ (M=Fe, Ni, Zn). <i>Journal of Physics Condensed Matter</i> , 1991, 3, 9169-9184.	0.7	18
75	Impact of Cu/III ratio on the near-surface defects in polycrystalline CuGaSe_2 thin films. <i>Applied Physics Letters</i> , 2011, 98, 112105.	1.5	18
76	Mechanism of covalency-induced electric polarization within the framework of maximally localized Wannier orbitals. <i>Physical Review B</i> , 2015, 91, .	1.1	18
77	A fully automated approach to calculate the melting temperature of elemental crystals. <i>Computational Materials Science</i> , 2021, 187, 110065.	1.4	18
78	First-Principles Study of the Stability and Interfacial Bonding of Tilt and Twist Grain Boundaries in Al and Cu. <i>Materials Transactions</i> , 2009, 50, 11-18.	0.4	17
79	Computational findings of metastable ferroelectric phases of squaric acid. <i>Physical Review B</i> , 2018, 97, .	1.1	17
80	Correlation analysis of strongly fluctuating atomic volumes, charges, and stresses in body-centered cubic refractory high-entropy alloys. <i>Physical Review Materials</i> , 2020, 4, .	0.9	17
81	Electronic States of Single-Component Molecular Conductors [<i>M</i> (tmdt) ₂]. <i>Journal of the Physical Society of Japan</i> , 2013, 82, 054711.	0.7	16
82	Exotic Ferroelectricity in Tetrathiafulvalene- <i>p</i> -Chloranil: Anomalous Effective Charges and a Picture in the Framework of Maximally Localized Wannier Orbitals. <i>Journal of the Physical Society of Japan</i> , 2014, 83, 073702.	0.7	16
83	Correlated Proton Transfer and Ferroelectricity along Alternating Zwitterionic and Nonzwitterionic Anthranilic Acid Molecules. <i>Chemistry of Materials</i> , 2015, 27, 6193-6197.	3.2	16
84	Vacancy-type defects in $\text{In}_x\text{Ga}_{1-x}\text{N}$ grown on GaN templates probed using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	15
85	Vacancy-type defects in bulk GaN grown by the Na-flux method probed using positron annihilation. <i>Journal of Crystal Growth</i> , 2017, 475, 261-265.	0.7	15
86	First-Principles Electronic-Structure Study for Organic Ferroelectric Tetrathiafulvalene- <i>p</i> -Bromanil. <i>Journal of the Physical Society of Japan</i> , 2010, 79, 043703.	0.7	14
87	(Invited) Point Defect Characterization of Group-III Nitrides by Using Monoenergetic Positron Beams. <i>ECS Transactions</i> , 2014, 61, 19-30.	0.3	14
88	Computational study of positron annihilation parameters for cation mono-vacancies and vacancy complexes in nitride semiconductor alloys. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 475401.	0.7	14
89	Multi-Orbital Molecular Compound (TTM-TTP)I ₃ : Effective Model and Fragment Decomposition. <i>Journal of the Physical Society of Japan</i> , 2011, 80, 013703.	0.7	13
90	First-Principles Study of Structural and Magnetic Properties of $\text{R}(\text{Fe,Ti})_{12}$ and $\text{R}(\text{Fe,Ti})_{12}\text{N}$ (R = Nd, Sm, Y)., 2015, , .		13

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91	Coexistence of normal and inverse deuterium isotope effects in a phase-transition sequence of organic ferroelectrics. RSC Advances, 2019, 9, 39662-39673.	1.7	13
92	Improved minority carrier lifetime in p-type GaN segments prepared by vacancy-guided redistribution of Mg. Applied Physics Letters, 2021, 119, .	1.5	13
93	Positronic probe of vacancy defects on surfaces of Au nanoparticles embedded in MgO. Physical Review B, 2001, 64, .	1.1	12
94	Schottky-barrier heights of metal/ α -SiC{0001} interfaces by first-principles calculations. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2972-2976.	0.8	12
95	First-principles electronic-band calculations on organic conductors. Science and Technology of Advanced Materials, 2009, 10, 024311.	2.8	12
96	Spin-canting in lightly electron-doped CaMnO ₃ . Physical Review B, 2012, 85, .	1.1	12
97	First-principles studies of spin-orbital physics in pyrochlore oxides. Journal of Physics Condensed Matter, 2019, 31, 323001.	0.7	12
98	Hydrogen-Bonded Architectures and Field-Induced Polarization Switching in Bridged Bis(benzimidazole) Crystals. Crystal Growth and Design, 2019, 19, 328-335.	1.4	12
99	Dopant activation process in Mg-implanted GaN studied by monoenergetic positron beam. Scientific Reports, 2021, 11, 20660.	1.6	12
100	Annealing behaviors of vacancy-type defects near interfaces between metal contacts and GaN probed using a monoenergetic positron beam. Applied Physics Letters, 2014, 105, 052108.	1.5	11
101	Electron capture by vacancy-type defects in carbon-doped GaN studied using monoenergetic positron beams. Thin Solid Films, 2017, 639, 78-83.	0.8	11
102	Ab initio pseudopotential calculation for (TMTSF) ₂ ClO ₄ . Journal of Physics Condensed Matter, 1999, 11, 2279-2283.	0.7	10
103	A Possible Ground State and Its Electronic Structure of LaFeAsO. Journal of the Physical Society of Japan, 2008, 77, 91-95.	0.7	10
104	Control of intrinsic defects in molecular beam epitaxy grown CuInSe ₂ . Journal of Crystal Growth, 1999, 201-202, 1061-1064.	0.7	9
105	First-Principles Calculations of Schottky Barrier Heights of Monolayer Metal/ α -SiC{0001} Interfaces. Materials Transactions, 2006, 47, 2690-2695.	0.4	9
106	Second-Order Perturbation Formula for Magnetocrystalline Anisotropy Using Orbital Angular Momentum Matrix. Journal of the Physical Society of Japan, 2014, 83, 044707.	0.7	9
107	Vacancy-type defects in Mg-doped GaN grown by ammonia-based molecular beam epitaxy probed using a monoenergetic positron beam. Journal of Applied Physics, 2016, 119, 245702.	1.1	9
108	Positron annihilation studies of the iron-substituted oxide superconductor YBa ₂ (Cu _{1-x} Fe _x) ₃ O _{7-y} . Journal of Physics Condensed Matter, 1990, 2, 3691-3696.	0.7	8

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109	Electron-positron momentum density in TTF-TCNQ. <i>Physical Review B</i> , 1997, 55, 2048-2055.	1.1	8
110	Ab initio electronic structure study for TTF-TCNQ under uniaxial compression. <i>Physical Review B</i> , 2004, 69, .	1.1	8
111	Structures and Physical Properties of Highly Conducting Single-Component Molecular Conductors Containing Se Atoms. <i>European Journal of Inorganic Chemistry</i> , 2009, 2009, 1585-1591.	1.0	8
112	Vacancy-type defects introduced by plastic deformation of GaN studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	8
113	Computational studies of positron states and annihilation parameters in semiconductors "vacancy-type defects in group-III nitrides". <i>Journal of Physics: Conference Series</i> , 2016, 674, 012020.	0.3	8
114	Single-Component Molecular Conductors "Multi-Orbital Correlated d-Electron Systems. <i>Bulletin of the Chemical Society of Japan</i> , 2021, 94, 2540-2562.	2.0	8
115	Large polarization and record-high performance of energy storage induced by a phase change in organic molecular crystals. <i>Chemical Science</i> , 2021, 12, 14198-14206.	3.7	8
116	Vacancy-impurity complexes in polycrystalline Si used as gate electrodes of HfSiON-based metal-oxide-semiconductors probed using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2006, 100, 034509.	1.1	7
117	Point defects introduced by InN alloying into $\text{In}_x\text{Ga}_{1-x}\text{N}$ probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2013, 113, 123502.	1.1	7
118	Metaelectric multiphase transitions in a highly polarizable molecular crystal. <i>Chemical Science</i> , 2020, 11, 6183-6192.	3.7	7
119	Effect of Ultra-High-Pressure Annealing on Defect Reactions in Ion-Implanted GaN Studied by Positron Annihilation. <i>Physica Status Solidi (B): Basic Research</i> , 2022, 259, .	0.7	7
120	Positron annihilation studies of superconductors with high transition temperatures. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1987, 148, 497-499.	0.9	6
121	In-situ X-ray photoemission spectroscopy of layered structure. <i>Journal of Physics and Chemistry of Solids</i> , 1993, 54, 1207-1210.	1.9	6
122	In-situ characterization of doping-effect on electronic structure of epitaxial films of infinite layer SrCuO_2 . <i>European Physical Journal D</i> , 1996, 46, 2683-2684.	0.4	6
123	Ab initio Pseudopotential Band Calculation of Organic Conductors. <i>Journal of Low Temperature Physics</i> , 1999, 117, 1753-1757.	0.6	6
124	Calculation of positron states in carbon-nanotube bundles. <i>Journal of Physics Condensed Matter</i> , 2002, 14, 9753-9762.	0.7	6
125	Electronic Structure of $\text{Cu}(\text{tmdt})_2$ Studied with First-Principles Calculations. <i>Crystals</i> , 2012, 2, 1210-1221.	1.0	6
126	Spin frustration, charge ordering, and enhanced antiferromagnetism in $\text{TMTTF}_2\text{SbF}_6$. <i>Physica B: Condensed Matter</i> , 2012, 407, 1783-1786.	1.3	6

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127	Computational Study of Positron Monovacancy Interaction in d-Block Metals. Journal of the Physical Society of Japan, 2015, 84, 083703.	0.7	6
128	Antiferromagnetic Mott insulating state in the single-component molecular material Pd(tmdt) <math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></math>. Physical Review B, 2017, 96, .	1.1	6
129	Polarity-dependence of the defect formation in c-axis oriented ZnO by the irradiation of an 8 MeV proton beam. Journal of Applied Physics, 2018, 123, 161562.	1.1	6
130	Hole capture-coefficient of intrinsic nonradiative recombination centers that commonly exist in bulk, epitaxial, and proton-irradiated ZnO. Journal of Applied Physics, 2020, 127, 215704.	1.1	6
131	Vacancy-type defects in bulk GaN grown by oxide vapor phase epitaxy probed using positron annihilation. Journal of Crystal Growth, 2021, 570, 126219.	0.7	6
132	Resonant tunneling driven metal-insulator transition in double quantum-well structures of strongly correlated oxide. Nature Communications, 2021, 12, 7070.	5.8	6
133	Calculations of positron states in fullerenes. Synthetic Metals, 1993, 56, 3074-3079.	2.1	5
134	Positron Lifetime Study on Semiconductor Thin Films. Materials Science Forum, 1997, 255-257, 714-717.	0.3	5
135	Calculation of positron states in C60. Physical Review B, 2003, 67, .	1.1	5
136	Vacancy-type defects in strained-Si layers deposited on SiGe/Si structures probed by using monoenergetic positron beams. Journal of Applied Physics, 2005, 97, 023532.	1.1	5
137	Vacancy-fluorine complexes and their impact on the properties of metal-oxide transistors with high-k gate dielectrics studied using monoenergetic positron beams. Journal of Applied Physics, 2007, 102, 054511.	1.1	5
138	Effect of V/III flux ratio on luminescence properties and defect formation of Er-doped GaN. Applied Physics Letters, 2010, 96, 051907.	1.5	5
139	First-Principles Electronic Structure of Superconductor Ca4Al2O6Fe2P2: Comparison with LaFePO and Ca4Al2O6Fe2As2. Journal of the Physical Society of Japan, 2012, 81, 014701.	0.7	5
140	Vacancy clusters introduced by CF4-based plasma treatment in GaN probed with a monoenergetic positron beam. Applied Physics Express, 2014, 7, 121001.	1.1	5
141	Reduced nonradiative recombination rates in c-plane Al0.83In0.17N films grown on a nearly lattice-matched GaN substrate by metalorganic vapor phase epitaxy. Applied Physics Letters, 2021, 119, .	1.5	5
142	Positron states in \hat{I}^2 -(BEDT-TTF)2I3. Solid State Communications, 1993, 85, 397-399.	0.9	4
143	Surface study of a, b-axis oriented YBa2Cu3O7 \hat{I} epitaxial thin films by in situ angle resolved x-ray photoemission spectroscopy. Applied Physics Letters, 1993, 63, 2967-2969.	1.5	4
144	A method of calculating k-dependent positron states based on the finite-difference approximation. Journal of Physics Condensed Matter, 1994, 6, L71-L74.	0.7	4

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145	Positron lifetimes in molecular crystals. Canadian Journal of Physics, 1996, 74, 534-539.	0.4	4
146	Thermal Equilibrium Defects in Anthracene Probed by Positron Annihilation. Japanese Journal of Applied Physics, 1996, 35, 3623-3629.	0.8	4
147	Calculation of Positron ACAR Spectra on C₆₀. Materials Science Forum, 1997, 255-257, 542-544.	0.3	4
148	Electron-positron momentum density in (TMTSF) ₂ ClO ₄ . Physical Review B, 1999, 60, R3747-R3750.	1.1	4
149	Ab initio calculation of positron distribution, ACAR and lifetime in TTF-TCNQ. Radiation Physics and Chemistry, 2000, 58, 437-441.	1.4	4
150	Ab initio electronic structure calculation for \pm 2D C_{60} . Physical Review B, 2002, 65, .	1.1	4
151	Point defects in GaN and related group-III nitrides studied by means of positron annihilation. Proceedings of SPIE, 2011, , .	0.8	4
152	Hydrogen-bonded single-component organic ferroelectrics revisited by van der Waals density-functional theory calculations. Physical Review Materials, 2021, 5, .	0.9	4
153	Positron distributions and lifetimes in novel superconductors. Journal of Physics and Chemistry of Solids, 1993, 54, 1247-1250.	1.9	3
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